



SOT-23 Plastic-Encapsulate Diodes

BAS116LT1

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^{\circ}C$)

Forward Current

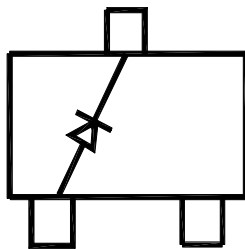
I_F : 200 mA

Reverse Voltage

V_R : 75 V

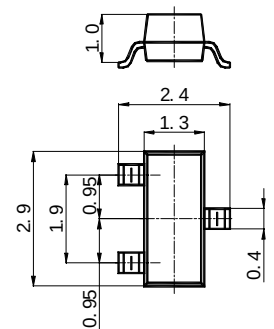
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



Marking JV

SOT-23



Unit : mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$		5	nA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		900 1000 1100 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		2	pF
Reverse recovery time	t_{rr}			3	μS